

**1. Scope :**

This specification applies to PIN silicon photodiode chips,  
Device No. PD-0062A

**2. Structure :**

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :  
 Top side (Anode ) : Aluminum alloy .  
 ( Cathode ) : Aluminum alloy.

**3. Size :**

- 3-1. Chip size : 63 mils × 63 mils ( 1.6 mm × 1.6 mm ).
- 3-2. Chip thickness : 12 ± 1.5 mils ( 0.305 ± 0.038 mm).
- 3-3. Active area : 53 mils × 53 mils ( 1.346 mm × 1.346 mm ).
- 3-4. Bonding pad ( Anode ) : 6 mils × 6 mils ( 0.153 mm × 0.153 mm ).  
 ( Cathode ) : 6 mils × 6 mils ( 0.153 mm × 0.153 mm ).
- 3-5. Pattern drawing : Refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
**Reverse dark Current	$I_D$	$V_R=20V$ $E_e=0mW/cm^2$			10	nA
**Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit Voltage	$V_{oc}$	$T=2856K$ $E_e=5mW/cm^2$		390		mV
Short circuit Current	$I_{sc}$	$T=2856K$ $E_e=5mW/cm^2$		12		$\mu A$
Reverse light Current	$I_L$	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		12		$\mu A$
Total Capacitance	$C_t$	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		6		pF

\*\*Based on 100% probing

